

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-13. (Canceled)

14. (Previously presented) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising CHF₃, argon and HCl or BCl₃, the gas formulation being free of SF₆.

15-17. (Canceled)

18. (Previously presented) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising CHF₃, argon and chlorine, the gas formulation being free of SF₆, and a ratio of flow rates of CHF₃:argon:chlorine in the formulation is 5 to 80 sccm:5 to 80 sccm:5 to 60 sccm.

19-20. (Canceled)

21. (Previously presented) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising (i) more than one fluorine-containing compound, (ii) an inert carrier gas selected from the group consisting of krypton, argon, neon, helium, and mixtures thereof, and (iii) chlorine, the gas formulation being free of SF₆.

22-27. (Canceled)

28. (Previously presented) The gas formulation of Claim 14, which comprises HCl.
29. (Previously presented) The gas formulation of Claim 14, which comprises BCl₃.
30. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is krypton.
31. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is argon.
32. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is neon.
33. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is helium.
34. (Canceled)
35. (Canceled)